

5/19/99

6/8/99
Offward
JC

S/N 09/135,413

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Examiner: Viet Q. Nguyen

Serial No.: 09/135,413

Group Art Unit: 2818

Filed: August 14, 1998

Docket: 303.354US2

Title: DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE
INSULATOR

AMENDMENT AND RESPONSE

Assistant Commissioner for Patents
Washington, D.C. 20231

In response to the Office Action mailed February 23, 1999, please amend the above
identified patent application as follows:

File = 7/29/97
6225668

IN THE TITLE

Please delete the title and replace it with the following: --Method For Operating A
DEAPROM Having An Amorphous Silicon Carbide Gate Insulator--.

IN THE SPECIFICATION

Please amend the specification by deleting lines 5-18 on page 1 of the originally filed
application, beginning with the heading "Cross Reference To Related Applications."

On page 19, lines 26-27, please replace "serial number ____" with --serial number
08/903,453--.

185.26

365

185.19

RECEIVED

MAY 25 1999

185.29

IN THE CLAIMS

Please cancel claims 25-27 and 39-42.

TECHNOLOGY CENTER 2800

185.01

Please amend the claims as follows:

257/ 77,319, 316

19. (Amended) A method of using a floating gate transistor having a floating gate electrode
and an adjacent amorphous silicon carbide (a-SiC) gate insulator between the floating gate
electrode and a substrate, the method comprising:

storing data by changing [the] a charge of the floating gate electrode;
reading data by detecting a current between a source and a drain in the substrate; and

05/21/1999 TTR:HL 00000011 09135413

156.00 CP
30.00 CP

01 22:132
02 22:103